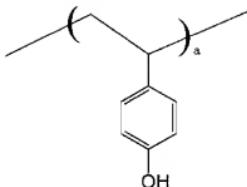


Amendments to the Claims:

This listing of claims will replace all prior versions, and listing, of claims in the application.

1. (Currently Amended) An organic anti-reflective composition comprising a crosslinking agent, a light absorbing agent, a thermal acid generator, an organic solvent and an adhesivity enhancer represented by the following Chemical Formula 1:

Chemical Formula 1

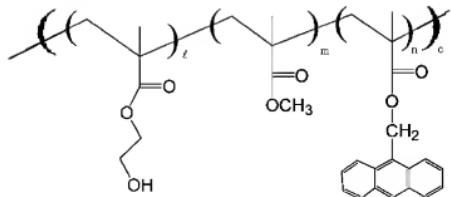


wherein

a is the degree of polymerization, ranging from 30 to 400,

wherein said light absorbing agent is the compound represented by the following Chemical Formula 3:

Chemical Formula 3



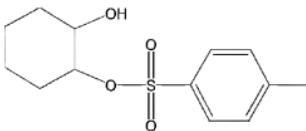
wherein

l, m and n are molar ratios: l ranging from 0.1 to 0.5, m ranging from 0.05 to 0.5, n ranging from 0.1 to 0.7, and l + m + n = 1; and

c is the degree of polymerization, ranging from 10 to 400,

wherein said thermal acid generator is the compound represented by the following Chemical

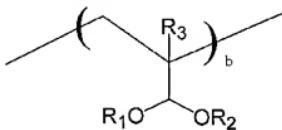
Formula 4:



and wherein said crosslinking agent is the

compound represented by the following Chemical Formula 2:

Chemical Formula 2



wherein

b is the degree of polymerization, ranging from 10 to 100;

each of R1 and R2 is C1 to C4 alkyl; and

R3 is hydrogen or methyl.

2. (Original) The organic anti-reflective composition according to Claim 1, which comprises:

- (a) 100 parts by weight of crosslinking agent;
- (b) 30 to 400 parts by weight of light absorbing agent;
- (c) 10 to 200 parts by weight thermal acid generator;
- (d) 30 to 400 parts by weight of adhesivity enhancer represented by Chemical Formula 1; and
- (e) 1,000 to 10,000 parts by weight of organic solvent.

3-5 (Cancelled).

6. (Original) A patterning method comprising the steps of

- (a) coating the organic anti-reflective composition according to Claim 1 on a part to be etched;

(b) crosslinking said organic anti-reflective composition by baking to form an organic anti-reflective film;

(c) coating a photoresist on said organic anti-reflective film, and exposing and developing the same to form a photoresist pattern; and

(d) etching the organic anti-reflective film with said photoresist pattern as mask.

7. (Original) The patterning method according to Claim 6, wherein said baking of the step (b) is carried out at 150 to 300 °C for 1 to 5 minutes.

8. (Original) The patterning method according to Claim 6, wherein baking is further carried out before and/or after exposure of the step (c).

9. (Original) The patterning method according to Claim 8, wherein said baking is carried out at 70 to 200 °C.

10. (Original) The patterning method according to Claim 6, wherein far UV such as F₂ laser (157 nm), ArF (193 nm), KrF (248 nm) and EUV (extremely ultraviolet); E-beam; X-ray; or ion beam is used as exposure light source in the step (c).

11. (Previously Presented) A semiconductor device prepared by any method according to Claims 6.

12. (Previously Presented) A semiconductor device prepared by any method according to Claims 7.

13. (Previously Presented) A semiconductor device prepared by any method according to Claims 8.

14. (Previously Presented) A semiconductor device prepared by any method according to Claims 9.

15. (Previously Presented) A semiconductor device prepared by any method according to
Claims 10.

16-21. (Cancelled)